



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

ATTY.'S DOCKET: 2001 P 14585 US

AF #1
2800
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#6/B
1/28/03
(1mo)

In re the application of:)
Chuan Lin)
Serial No.: 10/059,321 ✓)
Filing Date: January 31, 2002)
Title: REDUCTION OF NEGATIVE BIAS)
TEMPERATURE INSTABILITY IN)
NARROW WIDTH PMOS USING F₂)
IMPLANTATION)

Group Art: 2812
Examiner: I. Stanetta

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JAN 27 2003
TECHNOLOGY CENTER 2800

Amendment Under 37 C.F.R. §1.116

Assistant Commissioner for Patents
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed October 16, 2002
which rejected the claims in the above-identified patent
application, applicant respectfully request reconsideration
based upon the amendments hereinafter set forth.

A one month extension is requested and the fee therefor
in the amount of \$110.00 is enclosed herewith as check number
4617.

IN THE CLAIMS:

1. (Twice Amended) In a process of fabricating a narrow
channel width PMOSFET device, the improvement of affecting
reduction of negative bias temperature instability by use of
F₂ side wall implantation [and subsequent high density plasma
fill of a STI], comprising:

PLEASE DO NOT ENTER
1/30/03